

	U	Document ID	Title	Current OR
1	<input checked="" type="checkbox"/>	US 4921815 A	Method of producing a semiconductor memory device having trench capacitors	438/248
2	<input checked="" type="checkbox"/>	US 5153685 A	Semiconductor integrated circuit device having switching MISFET and capacitor element and method of producing the same, including wiring therefor and method of producing such wiring	257/296
3	<input checked="" type="checkbox"/>	US 5753550 A	Semiconductor integrated circuit device having switching MISFET and capacitor element and method of producing the same, including wiring therefor and method of producing such wiring	438/253
4	<input checked="" type="checkbox"/>	US 5792693 A	Method for producing capacitors having increased surface area for dynamic random access memory	438/254
5	<input type="checkbox"/>	US 5930624 A	Method of producing semiconductor integrated circuit device having switching MISFET and capacitor element including wiring	438/253
6	<input type="checkbox"/>	US 6281071 B1	Method of producing semiconductor integrated circuit device having switching MISFET and capacitor element including wiring therefor and method of producing such wiring	438/253
7	<input type="checkbox"/>	US 20020028574 A1	Semiconductor integrated circuit device having switching misfet and capacitor element and method of producing the same, including wiring therefor and method of producing such wiring	438/618

L Number	Hits	Search Text	DB	Time stamp
1	5	"capacitive electrode" near5 "semiconductor substrate"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/11 10:37
2	12	"capacitive electrode" with "semiconductor substrate"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/11 10:38
6	2	("capacitive electrode" with "semiconductor substrate") and "metal" and (oxidation or oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/11 10:45
7	15	("4367580" "4682402" "5185689" "5356826" "5500387" "5585303" "5591658" "5614431" "5618749" "5683931" "5716863" "5759887" "5792683" "5885862" "5970338").PN.	USPAT	2002/03/11 10:44
8	72983	method adj produc\$.ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/11 11:08
9	14	(method adj produc\$.ti.) adj oxidation.ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/11 11:08
14	351	(method adj produc\$.ti.) and (capacitor or capacitive).ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/11 11:10
18	30	((method adj produc\$.ti.) and (capacitor or capacitive).ti.) and electrode.ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/11 11:12
21	176	"capacitive electrode".ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/11 11:12
23	11	"capacitive electrode".ti. and method.ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/11 11:13
24	46	((method adj produc\$.ti.) and (capacitor or capacitive).ti.) and "semiconductor substrate"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/11 11:14
25	21	((method adj produc\$.ti.) and (capacitor or capacitive).ti.) and "semiconductor substrate") and metal and oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/11 11:14
26	11	((method adj produc\$.ti.) and (capacitor or capacitive).ti.) and "semiconductor substrate") and metal and oxide) and oxidation	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/11 11:14

27	10	(((method adj produc\$.ti.) and (capacitor or capacitive).ti.) and "semiconductor substrate") and metal and oxide) and oxidation) and (inhibiti or inhibiting or "slow down" or reduce or hamper)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/11 11:15
28	10	(((method adj produc\$.ti.) and (capacitor or capacitive).ti.) and "semiconductor substrate") and metal and oxide) and oxidation) and (inhibiti or inhibiting or "slow down" or reduce or hamper)) and layer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/11 11:16
29	8	((((method adj produc\$.ti.) and (capacitor or capacitive).ti.) and "semiconductor substrate") and metal and oxide) and oxidation) and (inhibiti or inhibiting or "slow down" or reduce or hamper)) and layer) and electrically	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/11 11:16
30	7	((((method adj produc\$.ti.) and (capacitor or capacitive).ti.) and "semiconductor substrate") and metal and oxide) and oxidation) and (inhibiti or inhibiting or "slow down" or reduce or hamper)) and layer) and electrically) and (conductive or conductor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/11 11:17